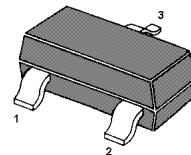


BCW68

PNP Silicon Epitaxial Planar Transistor

for high current application

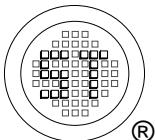
The transistor is subdivided into three groups F, G and H according to its DC current gain.



1. Base 2. Emitter 3. Collector
SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	$-V_{CBO}$	60	V
Collector Emitter Voltage	$-V_{CEO}$	45	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	800	mA
Peak Collector Current	$-I_{CM}$	1	A
Base Current	$-I_B$	100	mA
Peak Base Current	$-I_{BM}$	200	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$



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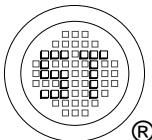


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BCW68

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_{CE} = 10 \text{ V}$, $-I_C = 100 \mu\text{A}$	F G H	h_{FE} h_{FE} h_{FE}	35 50 80	- - -	- - -
at $-V_{CE} = 1 \text{ V}$, $-I_C = 10 \text{ mA}$	F G H	h_{FE} h_{FE} h_{FE}	75 120 180	- - -	- - -
at $-V_{CE} = 1 \text{ V}$, $-I_C = 100 \text{ mA}$	F G H	h_{FE} h_{FE} h_{FE}	100 160 250	- - -	250 400 630
at $-V_{CE} = 2 \text{ V}$, $-I_C = 500 \text{ mA}$	F G H	h_{FE} h_{FE} h_{FE}	35 60 100	- - -	- - -
Collector Base Cutoff Current at $-V_{CB} = 45 \text{ V}$	$-I_{CBO}$	-	-	20	nA
Emitter Base Cutoff Current at $-V_{EB} = 4 \text{ V}$	$-I_{EBO}$	-	-	20	nA
Collector Base Breakdown Voltage at $-I_C = 10 \mu\text{A}$	$-V_{(BR)CBO}$	60	-	-	V
Collector Emitter Breakdown Voltage at $-I_C = 10 \text{ mA}$	$-V_{(BR)CEO}$	45	-	-	V
Emitter Base Breakdown Voltage at $-I_E = 10 \mu\text{A}$	$-V_{(BR)EBO}$	5	-	-	V
Collector Emitter Saturation Voltage at $-I_C = 100 \text{ mA}$, $-I_B = 10 \text{ mA}$ at $-I_C = 500 \text{ mA}$, $-I_B = 50 \text{ mA}$	$-V_{CE(sat)}$	- -	- -	0.3 0.7	V
Base Emitter Saturation Voltage at $-I_C = 100 \text{ mA}$, $-I_B = 10 \text{ mA}$ at $-I_C = 500 \text{ mA}$, $-I_B = 50 \text{ mA}$	$-V_{BE(sat)}$	- -	- -	1.25 2	V
Transition Frequency at $-V_{CE} = 5 \text{ V}$, $-I_C = 50 \text{ mA}$, $f = 100 \text{ MHz}$	f_T	-	200	-	MHz
Collector Base Capacitance at $-V_{CB} = 10 \text{ V}$, $f = 1 \text{ MHz}$	C_{ob}	-	6	-	pF



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